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November 2013

FQP13N06L

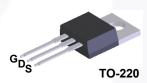
N-Channel QFET[®] MOSFET 60 V, 13.6 A, 110 m Ω

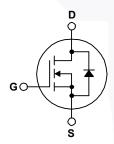
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 13.6 A, 60 V, $R_{DS(on)}$ = 110 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.8 A
- Low Gate Charge (Typ. 4.8 nC)
- Low Crss (Typ. 17 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP13N06L	Unit	
V_{DSS}	Drain-Source Voltage		60	V	
I _D	Drain Current - Continuous (T _C = 25°C)		13.6	А	
	- Continuous (T _C = 100°C)		9.6	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	54.4	Α	
V _{GSS}	Gate-Source Voltage		± 20	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	90	mJ	
I _{AR}	Avalanche Current	(Note 1)	13.6	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		7.0	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		45	W	
	- Derate above 25°C		0.3	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQP13N06L	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.35	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP13N06L	FQP13N06L	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	;	0.05		V/°C
I _{DSS}	Zees Oats Valtage Busin Ourset	V _{DS} = 60 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	Zero Gate Voltage Drain Current	V _{DS} = 48 V, T _C = 150°C			10	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.5	V
R _{DS(on)}	Static Drain-Source	V _{GS} = 10 V, I _D = 6.8 A		0.088	0.11	
On-Resistance		$V_{GS} = 5 \text{ V}, I_D = 6.8 \text{ A}$		0.110	0.14	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 6.8 A		7		S
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		270	350	pF
C _{oss}	Output Capacitance			95	125	pF
C _{rss}	Reverse Transfer Capacitance			17	23	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 6.8 A,		8	25	ns
t _r	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_{D} = 0.8 \text{ A},$ $R_{G} = 25 \Omega$		90	190	ns
t _{d(off)}	Turn-Off Delay Time	116 - 20 22		20	50	ns
t _f	Turn-Off Fall Time	(Note 4		40	90	ns
Qg	Total Gate Charge	V _{DS} = 48 V, I _D = 13.6 A,		4.8	6.4	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 5 V	/	1.6		nC
Q _{gd}	Gate-Drain Charge	(Note 4		2.7	/	nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings	·			
I _S	Maximum Continuous Drain-Source Diode Forward Current				13.6	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				54.4	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 13.6 A			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = 13.6 \text{ A},$		45		ns
11		1 4 1 400 44		,,,		113

Q_{rr}

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = $570 \, \mu H$, I_{AS} = $13.6 \, A$, V_{DD} = $25 \, V$, R_G = $25 \, \Omega$, starting T_J = $25^{\circ} C$. 3. I_{SD} $\leq 13.6 \, A$, di/dt $\leq 300 \, A/\mu s$, V_{DD} $\leq BV_{DSS}$, starting T_J = $25^{\circ} C$. 4. Essentially independent of operating temperature.

Reverse Recovery Charge

nC

45

 $dI_F / dt = 100 A/\mu s$

Typical Characteristics

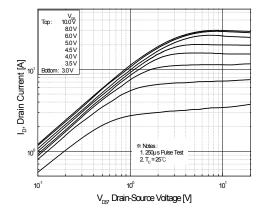


Figure 1. On-Region Characteristics

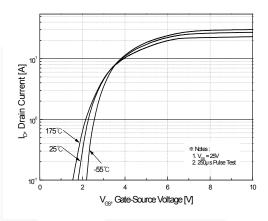


Figure 2. Transfer Characteristics

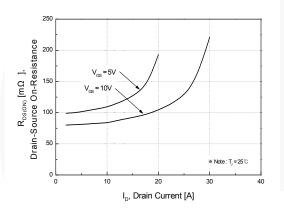


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

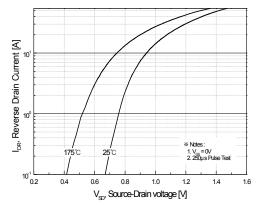


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

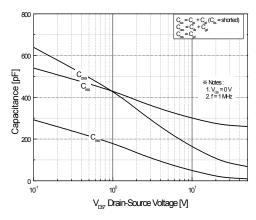


Figure 5. Capacitance Characteristics

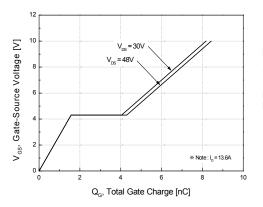


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

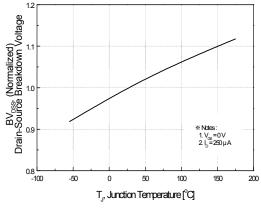


Figure 7. Breakdown Voltage Variation vs. Temperature

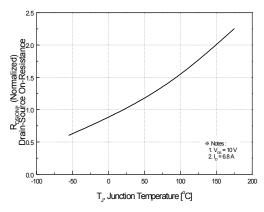


Figure 8. On-Resistance Variation vs. Temperature

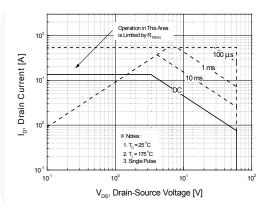


Figure 9. Maximum Safe Operating Area

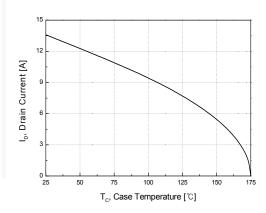


Figure 10. Maximum Drain Current vs. Case Temperature

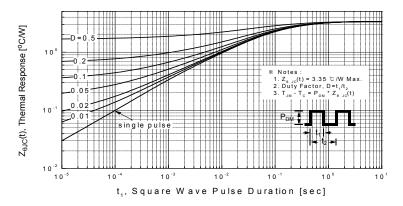


Figure 11. Transient Thermal Response Curve

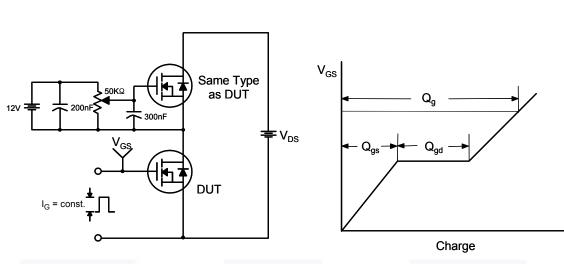


Figure 12. Gate Charge Test Circuit & Waveform

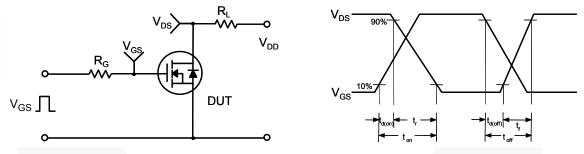


Figure 13. Resistive Switching Test Circuit & Waveforms

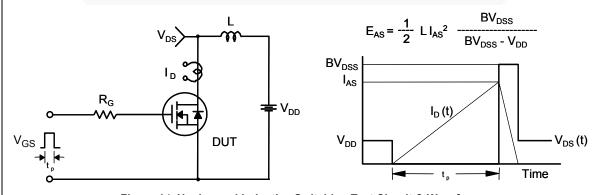
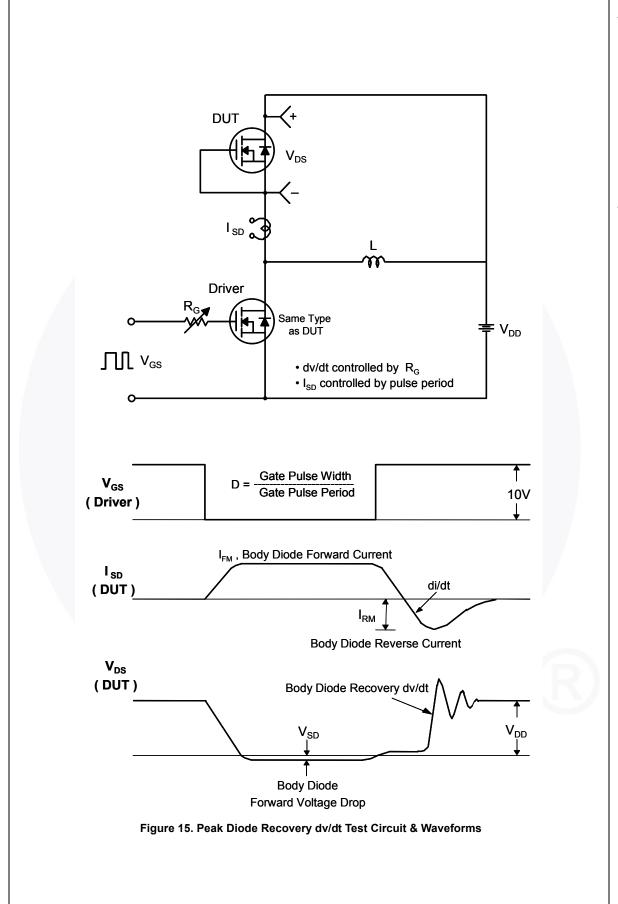


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

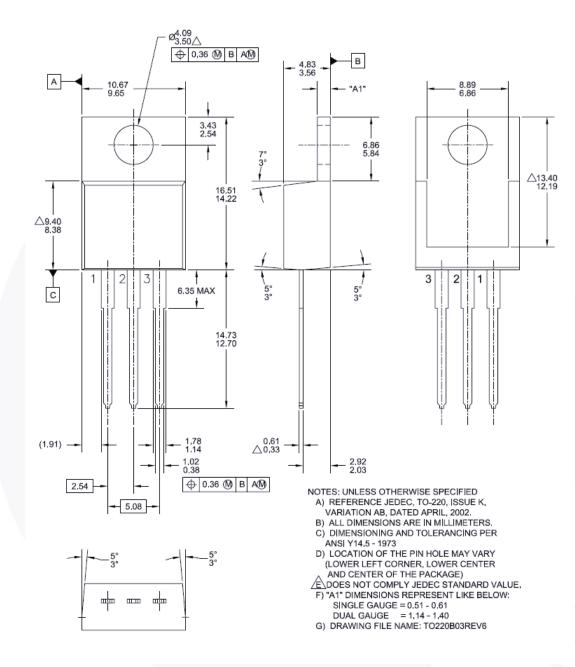


Figure 16 TO-220, Molded, 3-Lead, Jedec Variation AB

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